

Form PTO-1449		U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE			ATTY. DOCKET NO. MI22-2310	SERIAL NO. Unknown		
LIST OF ART CITED BY APPLICANT (Use several sheets if necessary)					APPLICANT: Brenda D. Kraus et al.			
					FILING DATE Filed Herewith	GROUP Unknown		
U.S. PATENT DOCUMENTS								
*Examiner's Initials		Document Number	Date	Name		Class	Subclass	Filing Date If Appropriate
BF	AM	10/133,947		Vaartstra				04/25/2002
	AB							
	AC							
	AD							
	AE							
	AF							
	AG							
	AH							
	AI							
FOREIGN PATENT DOCUMENTS								
		Document Number	Date	Country		Class	Subclass	Translation
	AJ							Yes
	AK							No
	AL							
OTHER REFERENCES (including Author, Title, Date, Pertinent Pages, Etc.)								
BF	AM		Baghurst et al., <i>Microwave syntheses for superconducting ceramics</i> , 332 NATURE 11 (March 24, 1988).					
BF	AN		Kuo et al., <i>Microwave-assisted chemical vapor deposition process for synthesizing carbon nanotubes</i> , J. VAC. SCI. TECHNOL., Vol. 19, No. 3, pp. 1030-1033 (May/June 2001).					
	AO							
EXAMINER <i>/Eric Fuller/</i>		DATE CONSIDERED 06/14/2006						
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Form PTO-1449 	U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE LIST OF ART CITED BY APPLICANT (Use several sheets if necessary)	ATTY. DOCKET NO. MI22-2310	SERIAL NO. 10/643,680
		APPLICANT: Kraus et al.	
		FILING DATE August 18, 2003	GROUP 1762

U.S. PATENT DOCUMENTS

*Examiner's Initials		Document Number	Date	Name	Class	Subclass	Filing Date If Appropriate
EF	AA	6,511,539	01/2003	Raaijmakers	117	102	
EF	AB	6,576,053	06/2003	Kim et al.	117	89	
EF	AC	6,753,618	06/2004	Basceri et al.	257	915	
EF	AD	6,780,704	08/2004	Raaijmakers	438	239	
EF	AE	2001/0024387 A1	09/2001	Raaijmakers	365	200	
EF	AF	2002/0182320 A1	12/2002	Leskela et al.	427	250	
EF	AG	2003/0049931 A1	03/2003	Byun et al.	438	649	
EF	AH	2003/0082296 A1	05/2003	Elers et al.	427	96	
EF	AI	2003/0116087 A1	06/2003	Nguyen et al.	118	715	

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		Document Number	Date	Country	Class	Subclass	Translation	
							Yes	No
EF	AA	WO 01/27346 A1	04/2001	WIPO				
	AK							
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OTHER REFERENCES (including Author, Title, Date, Pertinent Pages, Etc.)

EF	AM	Juppo et al., "Use of 1,1-Dimethylhydrazine in the Atomic Layer Deposition of Transition Metal Nitride Thin Films", <i>Journal of the Electrochemical Society</i> , 147 (9), 2000, p. 3377-3381.
EF	AN	H. Kim, "Atomic layer deposition of metal and nitride thin films: Current research efforts and applications for semiconductor device processing", <i>J. Vac. Sci. Technol. B</i> , Vol. 21, No. 6, Nov/Dec 2003, p. 2231-2261.
EF	AO	J. W. Klaus et al., Atomic Layer Deposition of Tungsten Nitride Films Using Sequential Surface Reactions", <i>Journal of the Electrochemical Society</i> , 147 (3), 2000, p. 1175-1181.
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EF	AA	2003/0168750 A1	09/2003	Basceri et al.	257	915	
EF	AB	2003/0205729 A1	11/2003	Basceri et al.	257	200	
	AC						
	AD						
	AE						
	AF						
	AG						
	AH						
	AI						

FOREIGN PATENT DOCUMENTS

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							Yes	No
	AJ							
	AK							
	AL							

OTHER REFERENCES (including Author, Title, Date, Pertinent Pages, Etc.)

EF	AN	J. W. Elam et al., "Surface chemistry and film growth during TiN atomic layer deposition using TDMAT and NH ₃ ", Elsevier Science B.V., 12 March 2003, p. 1-12.
EF	AN	Juppo, "Atomic Layer Deposition of Metal and Transition Metal Nitride Thin Films and In Situ Mass Spectrometry Studies", Univ. of Helsinki, Dept. of Chemistry, 14 Dec. 2001, p. 1-65.
	AO	
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Sheet 1 of 1

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EF	AA	6,863,725	03/05	Vaatstra et al.			
EF	AB	6,730,164	05/04	Vaatstra et al.			
EF	AC	6,730,163	05/04	Vaatstra et al.			
EF	AD	6,528,430	03/03	Kwan et al.			
	AE						
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	AG						
	AH						
	AI						
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